

FRED

$$\begin{aligned} V_{RRM} &= 600\text{ V} \\ I_{FAV} &= 2 \times 150\text{ A} \\ t_{rr} &= 35\text{ ns} \end{aligned}$$

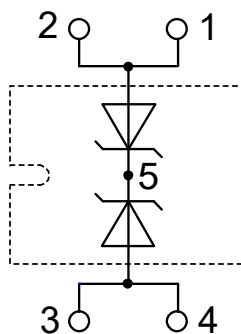
Fast Recovery Epitaxial Diode
 Extreme Low Loss and Soft Recovery
 Common Cathode

Part number

DSEK300-06A



Backside: cathode



Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low I_{rm} -values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low I_{rm} reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: SOT-227UI (minibloc)

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

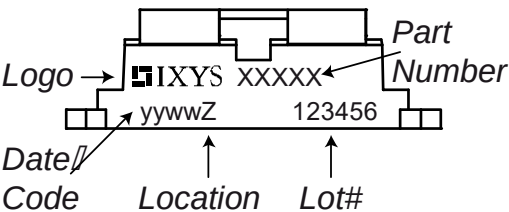
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Fast Diode				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V _{RSM}	max. non-repetitive reverse blocking voltage	T _{VJ} = 25°C				600	V
V _{RRM}	max. repetitive reverse blocking voltage	T _{VJ} = 25°C				600	V
I _R	reverse current, drain current	V _R = 600 V	T _{VJ} = 25°C			3	mA
		V _R = 480 V	T _{VJ} = 150°C			30	mA
V _F	forward voltage drop	I _F = 150 A	T _{VJ} = 25°C			1,17	V
		I _F = 300 A				1,40	V
		I _F = 150 A	T _{VJ} = 150°C			1,02	V
		I _F = 300 A				1,36	V
I _{FAV}	average forward current	T _C = 110°C rectangular d = 0.5	T _{VJ} = 150°C			150	A
V _{F0}	threshold voltage	} for power loss calculation only		T _{VJ} = 150°C		0,74	V
r _F	slope resistance					1,25	mΩ
R _{thJC}	thermal resistance junction to case					0,2	K/W
R _{thCH}	thermal resistance case to heatsink				0,1		K/W
P _{tot}	total power dissipation	T _C = 25°C				625	W
I _{FSM}	max. forward surge current	t = 10 ms; (50 Hz), sine; V _R = 0 V		T _{VJ} = 45°C		2,00	kA
C _J	junction capacitance	V _R = 400V f = 1 MHz		T _{VJ} = 25°C		214	pF
I _{RM}	max. reverse recovery current	} I _F = 150 A; V _R = 300 V -di _F /dt = 600 A/μs		T _{VJ} = 25°C		25	A
t _{rr}	reverse recovery time			T _{VJ} = 125°C		50	A
				T _{VJ} = 25°C		60	ns
				T _{VJ} = 125°C		180	ns

Package SOT-227UI (minibloc)			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			200	A
T_{VJ}	virtual junction temperature		-40		150	°C
T_{op}	operation temperature		-40		125	°C
T_{stg}	storage temperature		-40		150	°C
Weight				30		g
M_D	mounting torque		1,1		1,5	Nm
M_T	terminal torque		1,1		1,5	Nm

Product Marking

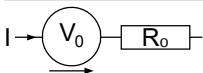


Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSEK300-06A	DSEK300-06A	Tube	10	517508

Equivalent Circuits for Simulation

* on die level

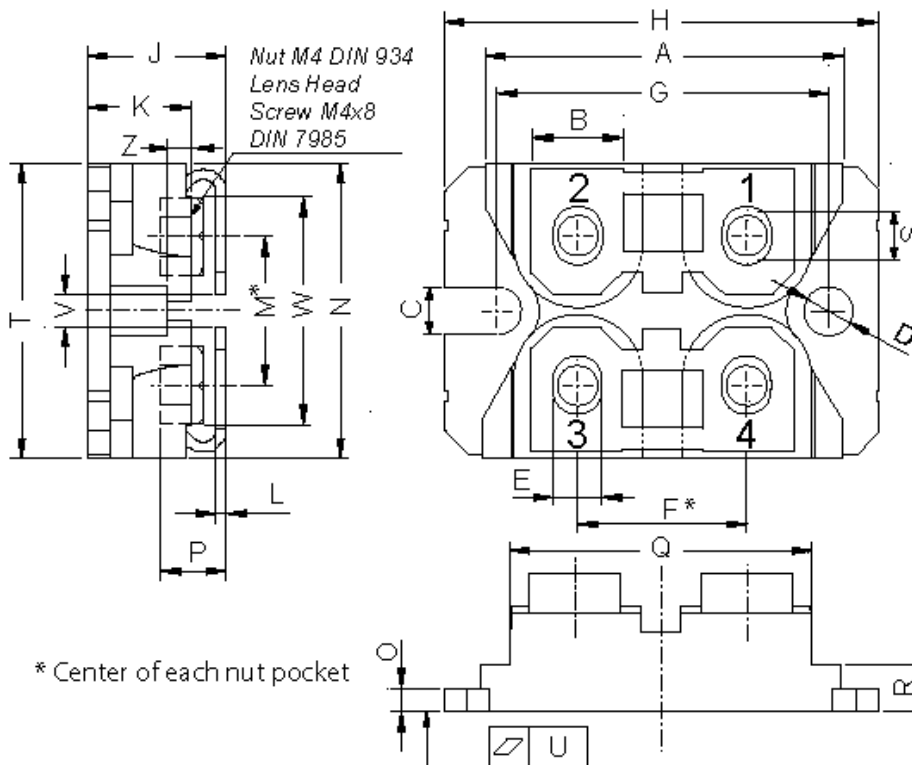
$T_{VJ} = 150^{\circ}C$



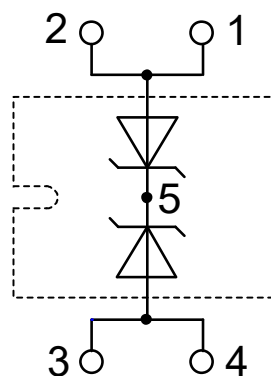
Fast Diode

$V_{0\ max}$
threshold voltage
0,74
V

$R_{0\ max}$
slope resistance *
0,75
mΩ

Outlines SOT-227UI (minibloc)


Dim.	Millimeter		Inches	
	min	max	min	max
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	37.80	38.23	1.488	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.74	0.84	0.029	0.033
M	12.50	13.10	0.492	0.516
N	25.15	25.42	0.990	1.001
O	1.95	2.13	0.077	0.084
P	4.95	6.20	0.195	0.244
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.167
S	4.55	4.85	0.179	0.191
T	24.59	25.25	0.968	0.994
U	-0.05	0.10	-0.002	0.004
V	3.20	5.50	0.126	0.217
W	19.81	21.08	0.780	0.830
Z	2.50	2.70	0.098	0.106



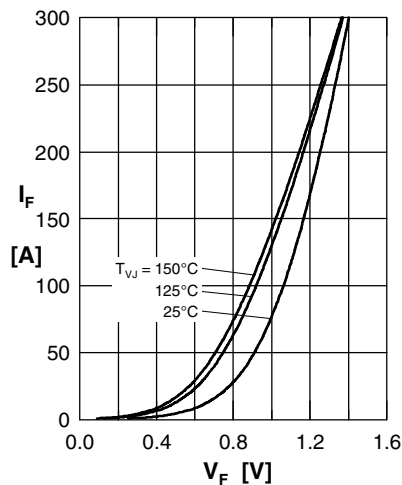
Fast Diode


Fig. 1 Forward current
 I_F versus V_F

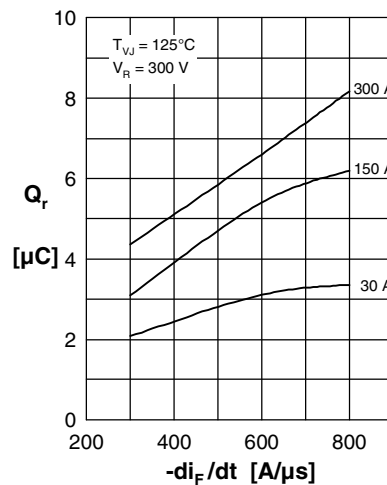


Fig. 2 Typ. reverse recov. charge
 Q_r versus $-di_F/dt$

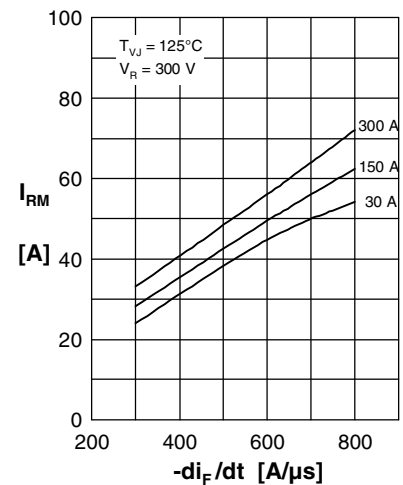


Fig. 3 Typ. peak reverse current
 I_{RM} versus $-di_F/dt$

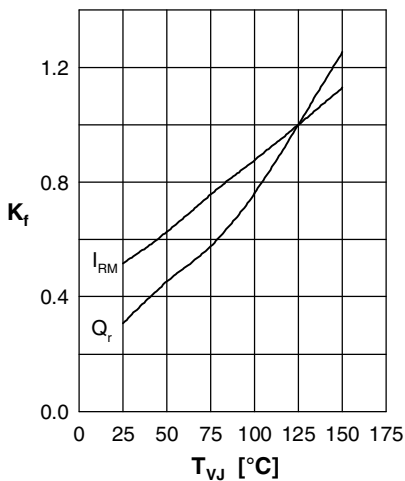


Fig. 4 Typ. dynamic parameters
 Q_r , I_{RM} versus T_{VJ}

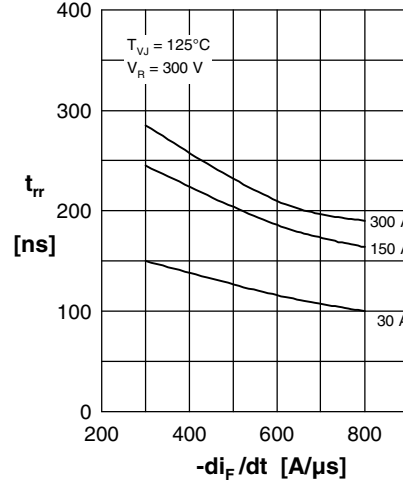


Fig. 5 Typ. recovery time
 t_{rr} versus $-di_F/dt$

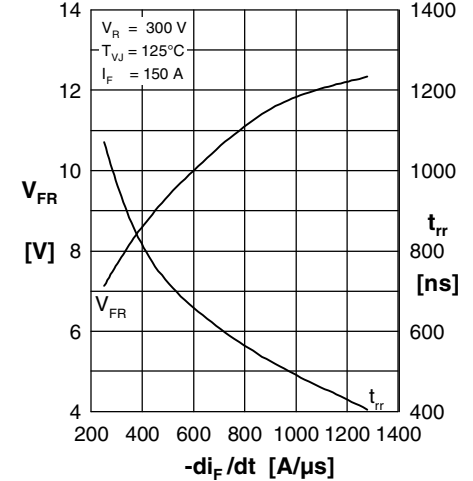


Fig. 6 Typ. peak forward voltage
 V_{FR} and t_{rr} versus $-di_F/dt$

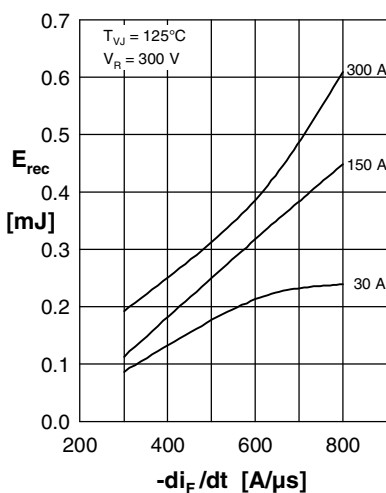


Fig. 7 Typ. recovery energy
 E_{rec} versus $-di_F/dt$

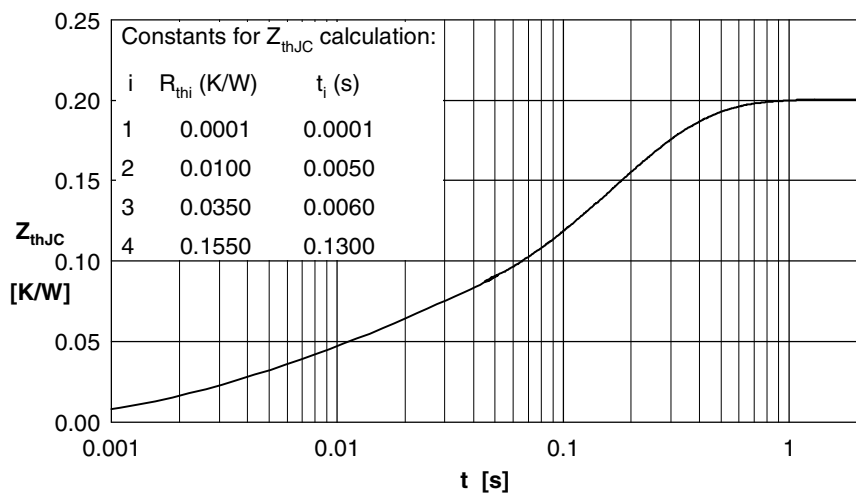


Fig. 8 Transient thermal resistance junction to case